

MM54HC75/MM74HC75 4-Bit Bistable Latch with Q and \bar{Q} Output

General Description

This 4-bit latch utilizes advanced silicon-gate CMOS technology to achieve the high noise immunity and low power consumption normally associated with standard CMOS integrated circuits. These devices can drive 10 LS-TTL loads.

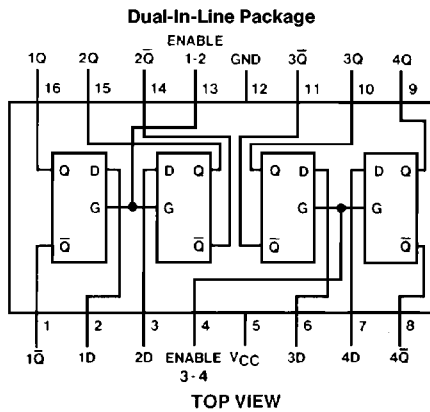
This latch is ideally suited for use as temporary storage for binary information processing, input/output, and indicator units. Information present at the data (D) input is transferred to the Q output when the enable (G) is high. The Q output will follow the data input as long as the enable remains high. When the enable goes low, the information that was present at the data input at the time the transition occurred is retained at the Q output until the enable is permitted to go high again.

The 54HC/74HC logic family is functionally as well as pin-out compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical operating frequency: 50 MHz
- Typical propagation delay: 12 ns
- Wide operating supply voltage range: 2–6V
- Low input current: 1 μ A maximum
- Low quiescent supply current: 80 μ A maximum (74HC Series)
- Fanout of 10 LS-TTL loads

Connection and Logic Diagrams

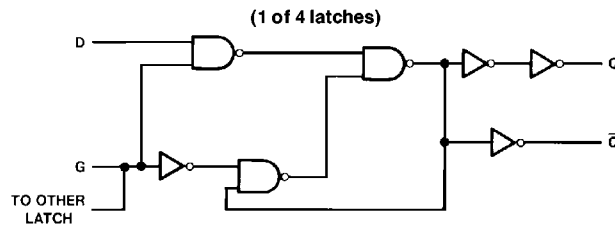


Truth Table

Inputs		Outputs	
D	G	Q	\bar{Q}
L	H	L	H
H	H	H	L
X	L	Q_0	\bar{Q}_0

H = High Level; L = Low Level
 X = Don't Care
 Q_0 = The level of Q before the transition of G

Order Number MM54HC75 or MM74HC75



Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	-0.5 to +7.0V
DC Input Voltage (V_{IN})	-1.5 to $V_{CC} + 1.5V$
DC Output Voltage (V_{OUT})	-0.5 to $V_{CC} + 0.5V$
Clamp Diode Current (I_{IK}, I_{OK})	± 20 mA
DC Output Current, per pin (I_{OUT})	± 25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	± 50 mA
Storage Temperature Range (T_{STG})	-65°C to +150°C
Power Dissipation (P_D) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times (t_r, t_f)			
$V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$		74HC	54HC	Units
						$T_A = -40$ to $85^\circ C$	$T_A = -55$ to $125^\circ C$	
				Typ		Guaranteed Limits		
V_{IH}	Minimum High Level Input Voltage		2.0V		1.5	1.5	1.5	V
			4.5V		3.15	3.15	3.15	V
			6.0V		4.2	4.2	4.2	V
V_{IL}	Maximum Low Level Input Voltage**		2.0V		0.5	0.5	0.5	V
			4.5V		1.35	1.35	1.35	V
			6.0V		1.8	1.8	1.8	V
V_{OH}	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 20 \mu A$	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 4.0$ mA $ I_{OUT} \leq 5.2$ mA	4.5V	4.2	3.98	3.84	3.7	V
			6.0V	5.7	5.48	5.34	5.2	V
V_{OL}	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 20 \mu A$	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 4.0$ mA $ I_{OUT} \leq 5.2$ mA	4.5V	0.2	0.26	0.33	0.4	V
			6.0V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		± 0.1	± 1.0	± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		4.0	40	80	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of $5V \pm 10\%$ the worst case output voltages (V_{OH} , and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at $V_{CC} = 5.5V$ and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} , and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

** V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $V_{CC}=5V, T_A=25^{\circ}C, C_L=15\text{ pF}, t_r=t_f=6\text{ ns}$

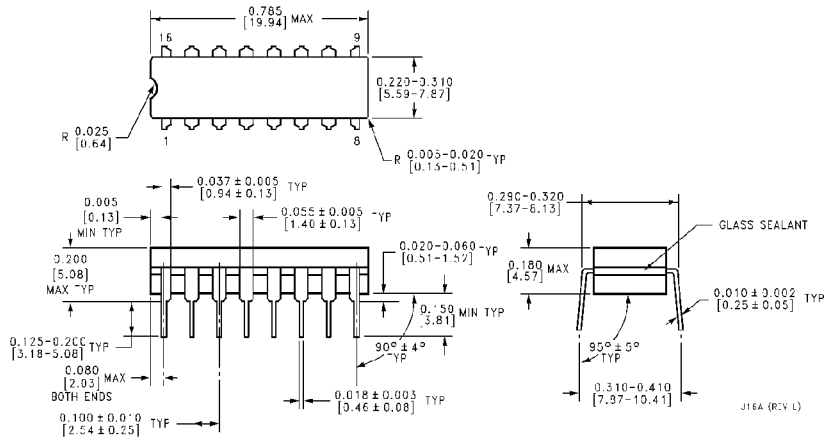
Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Data to Q		14	23	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Data to \bar{Q}		10	20	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Enable to Q		16	27	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Enable to \bar{Q}		11	23	ns
t_s	Minimum Set Up Time			20	ns
t_H	Minimum Hold Time		-2	0	ns
t_W	Minimum Pulse Width			16	ns

AC Electrical Characteristics $C_L=50\text{ pF}, t_r=t_f=6\text{ ns}$ (unless otherwise specified)

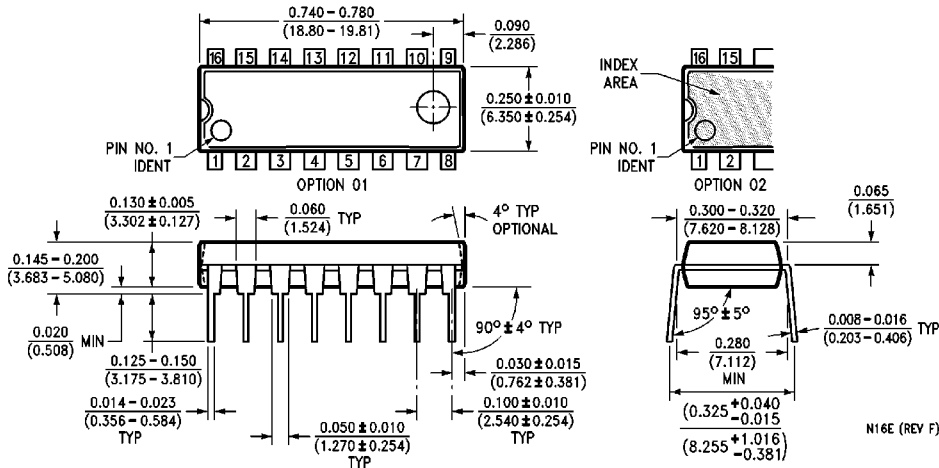
Symbol	Parameter	Conditions	V_{CC}	$T_A=25^{\circ}C$		74HC	54HC	Units
						$T_A=-40\text{ to }85^{\circ}C$	$T_A=-55\text{ to }125^{\circ}C$	
				Typ	Guaranteed Limits			
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Data to Q		2.0V	37	125	156	188	ns
			4.5V	15	25	32	38	ns
			6.0V	14	24	27	32	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Data to \bar{Q}		2.0V	29	110	138	165	ns
			4.5V	12	22	28	33	ns
			6.0V	11	19	24	29	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Enable to Q		2.0V	40	145	181	218	ns
			4.5V	18	29	36	44	ns
			6.0V	16	25	31	38	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Enable to \bar{Q}		2.0V	36	125	156	188	ns
			4.5V	15	25	31	38	ns
			6.0V	14	22	28	33	ns
t_s	Minimum Set Up Time Data to Enable		2.0V	40	100	125	150	ns
			4.5V	10	20	25	30	ns
			6.0V	9	17	21	25	ns
t_H	Minimum Hold Time Enable to Data		2.0V	-10	0	0	0	ns
			4.5V	-2	0	0	0	ns
			6.0V	-2	0	0	0	ns
t_W	Minimum Enable Pulse Width		2.0V	40	80	100	120	ns
			4.5V	11	16	20	24	ns
			6.0V	9	14	18	21	ns
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0V	25	75	95	110	ns
			4.5V	7	15	19	22	ns
			6.0V	6	13	16	19	ns
C_{PD}	Power Dissipation Capacitance (Note 5)	(per commonly clocked latched pair)		40				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Physical Dimensions inches (millimeters)



**Order Number MM54HC75J or MM74HC75J
NS Package J16A**



**Order Number MM54HC75N
NS Package N16E**

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